

**Data Sheet** 

SST12LP20 is a RF-matched power amplifier module based on the highly-reliable InGaP/GaAs HBT technology. This amplifier includes DC blocks and provides both input and output match to  $50\Omega$ . Operating over the 2.4–2.5 GHz frequency band, the amplifier typically provides 30 dB gain with 28% power-added efficiency at 21 dBm. SST12LP20 has excellent linearity with typically 18 dBm at 3% EVM for 54 Mbps 802.11g modulation, while meeting 802.11g spectrum mask at 21 dBm. It requires only two external bias components, and features easy board-level usage, along with high-speed power-up/down control through a single combined reference voltage pin. SST12LP20 is offered in an 8-contact USON package.

#### **Features**

- · High gain:
  - Typically 30 dB gain across 2.4-2.5 GHz over temperature 0°C to +85°C and 29 dB gain from -40°C to 0°C
- High linear output power:
  - ->24 dBm P1dB
  - Single-tone measurement. Please refer to "Absolute

  - Single-tone measurement. Please refer to Absolute Maximum Stress Ratings" on page 5

     Meets 802.11g OFDM ACPR requirement up to 21 dBm

     ~3% added EVM up to 18 dBm for 54 Mbps 802.11g signal 802.11n HT20 ACPR requirement up to 18 dBm

     Meets 802.11b ACPR requirement up to 21 dBm
- High power-added efficiency/Low operating current for 802.11b/g/n applications
  - $\sim 28\%/138 \text{ mA} @ P_{OUT} = 21 \text{ dBm for } 802.11 \text{ b/g}$
- Single-pin low I<sub>REF</sub> power-up/down control
  - $-I_{REF}$  < 2 mA
- Low idle current
  - -~78 mA Ico
- · High-speed power-up/down
  - Turn on/off time (10%- 90%) <100 ns
  - Typical power-up/down delay with driver delay included <200 ns
- Low shut-down current (~2 μA)

- Small variation over temperature
  - -~1 dB gain/power variation between 0°C to +85°C
- Excellent on-chip power detection
  - ->15 dB dynamic range, dB-wise Linear Temperature stable and load insensitive
- Input port matched to  $50\Omega$  internally
- · Both input and output ports are DC decoupled.
- Packages available
  - 8-contact USON 2mm x 2mm x 0.55mm
- All non-Pb (lead-free) devices are RoHS compliant

#### **Applications**

- WLAN (IEEE 802.11b/g/n)
- Home RF
- Cordless phones
- 2.4 GHz ISM wireless equipment



**Data Sheet** 

#### **Product Description**

SST12LP20 is a versatile power amplifier based on the highly-reliable InGaP/GaAs HBT technology. The device's input and output ports are matched to  $50\Omega$  internally. Both input and output ports are DC-decoupled and do not require DC-blocking capacitors. This helps reduce the system board's Bill of Materials (BOM) cost.

The SST12LP20 is a 2.4 GHz high-efficiency Power Amplifier designed in compliance with IEEE 802.11b/g/n applications. It typically provides 30 dB gain with 28% power-added efficiency (PAE) @ POUT = 21 dBm for 802.11b/g.

The SST12LP20 has excellent linearity, typically ~3% added EVM at 18 dBm output power which is essential for 54 Mbps 802.11g operation while meeting 802.11g spectrum mask at 21 dBm and 802.11b spectrum mask at 21 dBm.

The SST12LP20 also features easy board-level usage along with high-speed power-up/down control through a single combined reference voltage pin. Ultra-low reference current (total I<sub>REF</sub> ~2 mA) makes the SST12LP20 controllable by an on/off switching signal directly from the baseband chip. These features, coupled with low operating current, make the SST12LP20 ideal for the final stage power amplification in battery-powered 802.11b/g/n WLAN transmitter applications.

The SST12LP20 has an excellent on-chip, single-ended power detector, which features wide-range (>15 dB) with dB-wise linear. The excellent on-chip power detector provides a reliable solution to board-level power control.

The SST12LP20 is offered in 8-contact USON package. See Figure 2 for pin assignments and Table 1 for pin descriptions.



Data Sheet

#### **Functional Blocks**

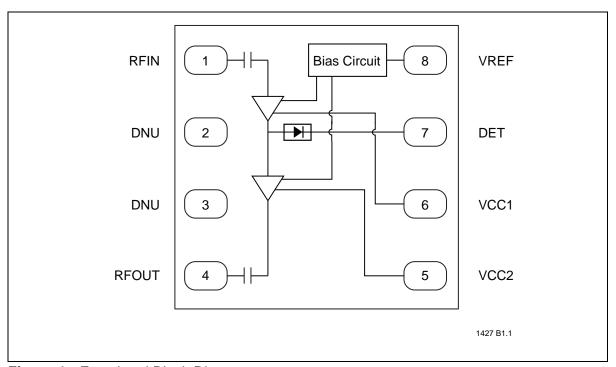


Figure 1: Functional Block Diagram



**Data Sheet** 

### **Pin Assignments**

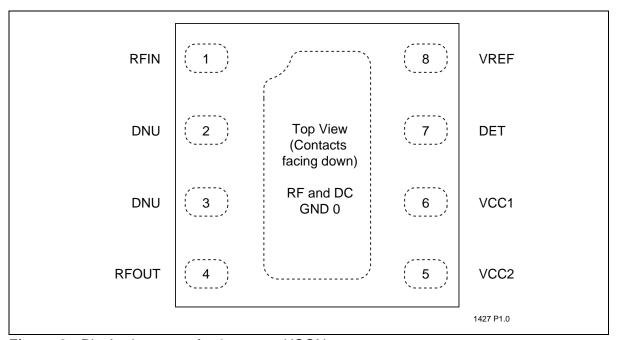


Figure 2: Pin Assignments for 8-contact USON

### **Pin Descriptions**

Table 1: Pin Description

Symbol	Pin No.	Pin Name	Type <sup>1</sup>	Function	
GND	0	Ground		Low inductance ground pad	
RFIN	1		ı	RF input, DC decoupled	
DNU	2	Do Not Use		Do not use or connect	
DNU	3	Do Not Use		Do not use or connect	
RFOUT	4		0	RF output, DC decoupled	
VCC2	5	Power Supply	PWR	Power Supply, 2 <sup>nd</sup> stage	
VCC1	6	Power Supply	PWR	Power Supply, 1 <sup>st</sup> stage	
DET	7		0	On-chip power detector	
VREF	8		PWR	1 <sup>st</sup> and 2 <sup>nd</sup> stage idle current control	

T1.0 75049

1. I=Input, O=Output



**Data Sheet** 

### **Electrical Specifications**

The RF and DC specifications for the power amplifier interface signals. Refer to Table 3 for the DC voltage and current specifications, Table 4 for RF specifications, and Figures 3 through 8 for the RF performance.

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under "Absolute Maximum Stress Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure beyond absolute maximum stress rating conditions may affect device reliability.)

Input power to pin 1 (P <sub>IN</sub> )	+5 dBm
Average output power from pin 4 (P <sub>OUT</sub> ) <sup>1</sup>	+25.5 dBm
Supply Voltage at pins 5 and 6(V <sub>CC</sub> )	0.3V to +4.8V
Reference voltage to pin 8 (V <sub>REF</sub> )	0.3V to +4.0V
DC supply current (I <sub>CC</sub> ) <sup>2</sup>	350 mA
Operating Temperature (T <sub>A</sub> )	40°C to +85°C
Storage Temperature (T <sub>STG</sub> )	40°C to +120°C
Maximum Junction Temperature (T <sub>J</sub> )	+150°C
Surface Mount Solder Reflow Temperature	260°C for 10 seconds

<sup>1.</sup> Never measure with CW source. Pulsed single-tone source with <50% duty cycle is recommended. Exceeding the maximum rating of average output power could cause permanent damage to the device.

#### **Table 2:** Operating Range

Range	Ambient Temp	$V_{DD}$
Industrial	-40°C to +85°C	3.3V

T2.1 75049

Table 3: DC Electrical Characteristics at 25°C

Symbol	Parameter	Min.	Тур	Max.	Unit
$V_{CC}$	Supply Voltage at pins 5 and 6	3.0	3.3	4.2	V
I <sub>CQ</sub>	Idle current to meet EVM ~3% @ 18 dBm Output Power, 802.11g OFDM 54 Mbps signal		75		mA
$V_{REG}$	Reference Voltage for pin 8	3.05	3.10	3.15	V
Icc	Current consumption to meet 802.11g OFDM 54 Mbps spectrum mask @ 21 dBm		140		mA
	Current consumption to meet 802.11b DSSS 54 Mbps spectrum mask @ 21 dBm		140		mA
	Current consumption to meet EVM ~3% @ 18 dBm Output Power with 802.11g OFDM 54 Mbps signal		110		mA

T3.1 75049

<sup>2.</sup> Measured with 100% duty cycle 54 Mbps 802.11g OFDM Signal



Data Sheet

Table 4: RF Characteristics at 25°C

Symbol	Parameter	Min.	Тур	Max.	Unit
F <sub>L-U</sub>	Frequency range	2412		2484	MHz
G	Small signal gain	28	30		dB
G <sub>VAR1</sub>	Gain variation over band (2412–2484 MHz)			±0.5	dB
G <sub>VAR2</sub>	Gain ripple over channel (20 MHz)		0.2		dB
2f, 3f, 4f, 5f	Harmonics at 22 dBm, without external filters		-25		dBc
EVM	Added EVM @ 18 dBm output with 802.11g OFDM 54 Mbps signal		3		%
P <sub>OUT</sub>	Output Power to meet 802.11g OFDM 54 Mbps spectrum mask	20	21		dBm
	Output Power to meet 802.11b DSSS 1 Mbps spectrum mask	20	21		dBm
	Output Power to meet 802.11n HT20 65 Mbps spectrum mask	18	20		dBm

T4.2 75049



**Data Sheet** 

### **Typical Performance Characteristics**

Test Conditions:  $V_{CC} = 3.3V$ ,  $T_A = 25$ °C, unless otherwise specified

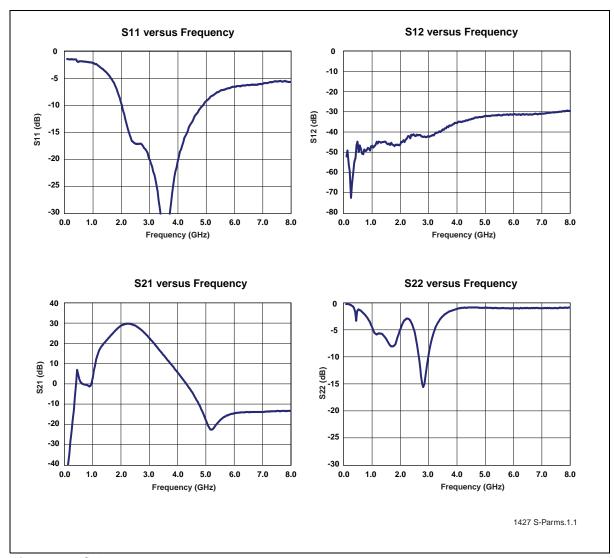


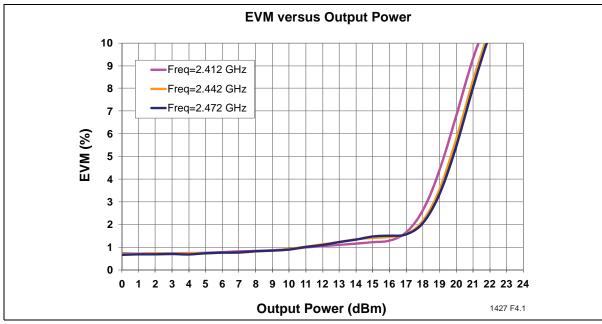
Figure 3: S-Parameters



**Data Sheet** 

### **Typical Performance Characteristics**

Test Conditions: V<sub>CC</sub> = 3.3V, T<sub>A</sub> = 25°C, 54 Mbps 802.11g OFDM Signal



**Figure 4:** EVM versus Output Power measured with Equalizer Channel Estimation set to "Sequence Only"

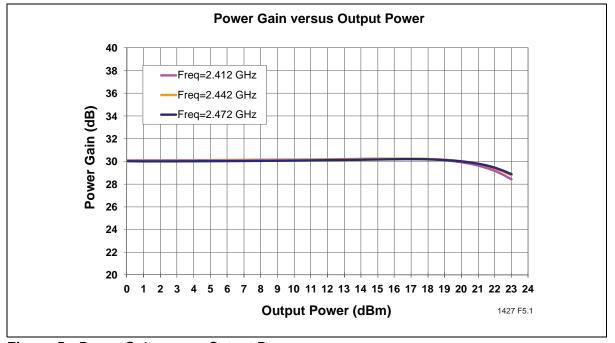


Figure 5: Power Gain versus Output Power



**Data Sheet** 

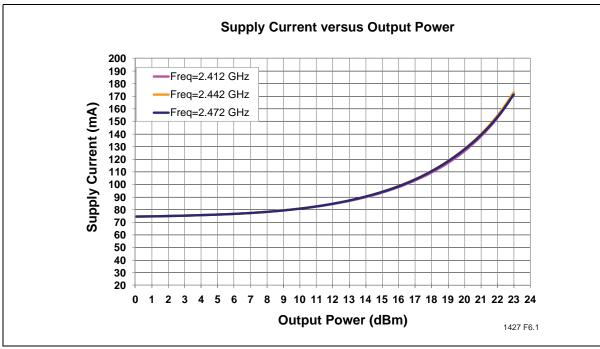


Figure 6: Total Current Consumption for 802.11g operation versus Output Power

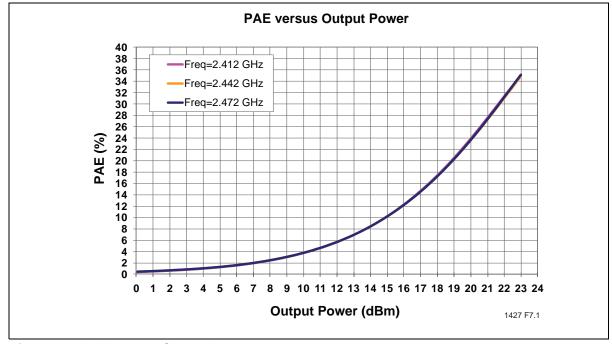


Figure 7: PAE versus Output Power



**Data Sheet** 

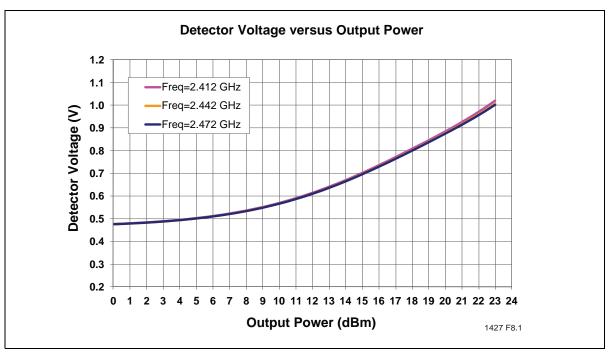


Figure 8: Detector Characteristics versus Output Power

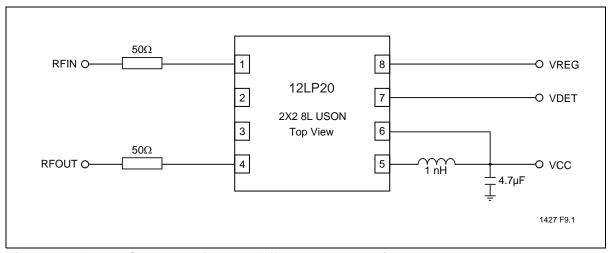
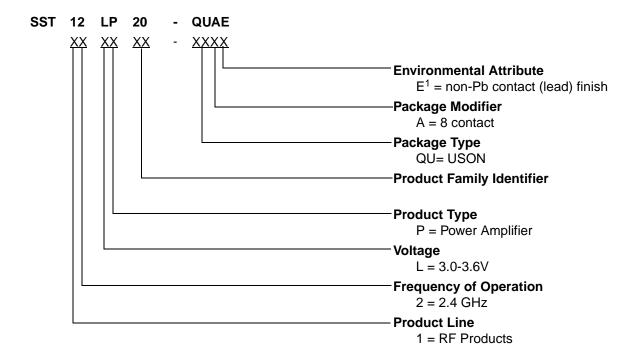


Figure 9: Typical Schematic for High-Efficiency 802.11b/g Applications



**Data Sheet** 

### **Product Ordering Information**



#### Valid combinations for SST12LP20

SST12LP20-QUAE

#### SST12LP20 Evaluation Kits

SST12LP20-QUAE-K

**Note:**Valid combinations are those products in mass production or will be in mass production. Consult your SST sales representative to confirm availability of valid combinations and to determine availability of new combinations.

Environmental suffix "E" denotes non-Pb solder. SST non-Pb solder devices are "RoHS Compliant".



**Data Sheet** 

### **Packaging Diagrams**

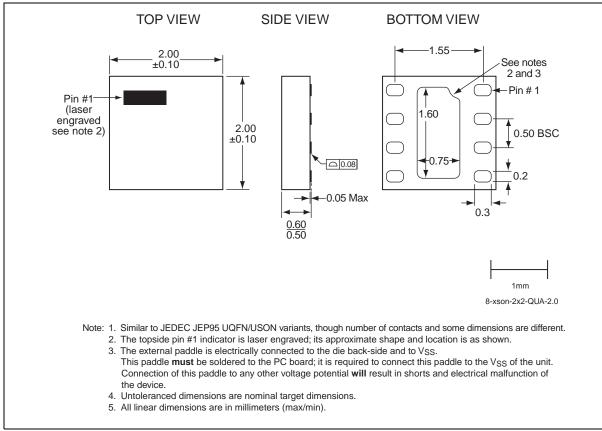


Figure 10:8-Contact Ultra-thin Small Outline No-lead (USON) SST Package Code: QUA



**Data Sheet** 

#### Table 5: Revision History

Revision	Description	Date		
00	Initial release of data sheet	May 2010		
Α	Revised "Features" on page 1 and "Product Description" on page 2  Jan  Jan  Jan  Jan  Jan  Jan  Jan  Ja			
	<ul> <li>Updated Figure 1 and Figures 3-9</li> </ul>			
	Modified Tables 3 and 4			
	Applied new document format			
	Released document under letter revision system			
	<ul> <li>Updated Spec number from S71427 to DS75049</li> </ul>			
В	<ul> <li>Revised maximum Reference voltage from 3.3V to 4.0V in "Al Maximum Stress Ratings" on page 5</li> </ul>	bsolute Apr 2012		
	Updated Figure 10 on page 12			
С	<ul> <li>Changed the document status from "Preliminary Specification "Data Sheet"</li> </ul>	n" to May 2013		

#### ISBN:978-1-62077-210-2

© 2013 Silicon Storage Technology, Inc-a Microchip Technology Company. All rights reserved.

SST, Silicon Storage Technology, the SST logo, SuperFlash, MTP, and FlashFlex are registered trademarks of Silicon Storage Technology, Inc. MPF, SQI, Serial Quad I/O, and Z-Scale are trademarks of Silicon Storage Technology, Inc. All other trademarks and registered trademarks mentioned herein are the property of their respective owners.

Specifications are subject to change without notice. Refer to www.microchip.com for the most recent documentation. For the most current package drawings, please see the Packaging Specification located at http://www.microchip.com/packaging.

Memory sizes denote raw storage capacity; actual usable capacity may be less.

SST makes no warranty for the use of its products other than those expressly contained in the Standard Terms and Conditions of Sale.

For sales office locations and information, please see www.microchip.com.

Silicon Storage Technology, Inc. A Microchip Technology Company www.microchip.com

### **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Microchip: SST12LP20-QUAE